

Transient Liquid Assisted Growth (TLAG)

A method to increase CC throughput and meet applications requirements

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Institut de Ciència de Materials de Barcelona, ICMAB-CSIC, Spain

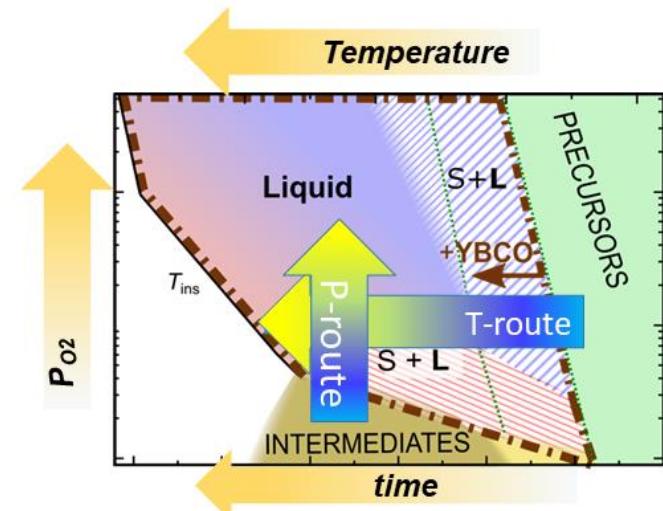
C. Mocuta

Diffabs beamline, Soleil Synchrotron, Paris, France



E. Solano

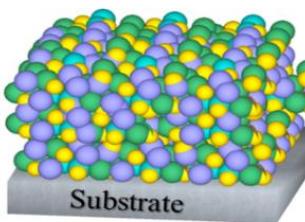
NCD-Sweet beamline, ALBA Synchrotron, Barcelona, Spain



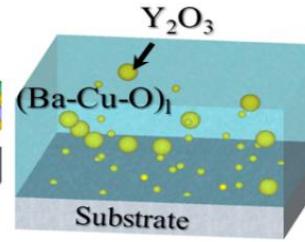
TRANSIENT LIQUID ASSISTED GROWTH: TLAG

A high throughput non-equilibrium kinetically controlled growth process

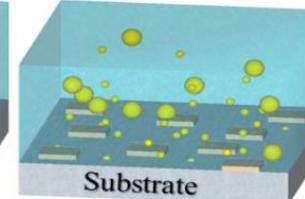
DEPOSITION
METHOD



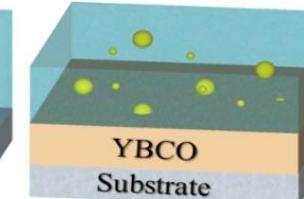
Nanocrystalline
precursors



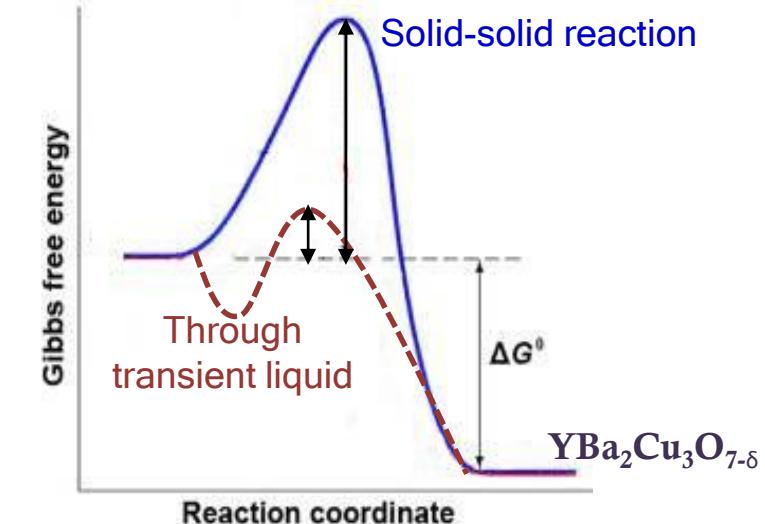
Transient liquid
+ Y_2O_3



YBCO
nucleation

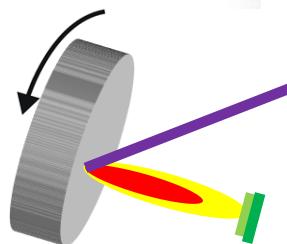


YBCO
growth



$\text{BaCO}_{3(\text{s})} + \text{CuO}_{(\text{s})} + \text{Y}_2\text{O}_{3(\text{s})}$ **TLAG-CSD**
FF metal-organic solution

L. Saltarelli et al, ACS Appl. Mat. & Interf. (2022)



$(\text{Ba}-\text{Cu}^{\text{III}}\text{-O})_{\text{s}} + \text{Cu}_2\text{O}_{(\text{s})} + \text{Y}_2\text{O}_{3(\text{s})}$ **TLAG-CSD**
REBCO target deposited at low T and P_{O_2}

A. Quetalto et al, SUST (2023)

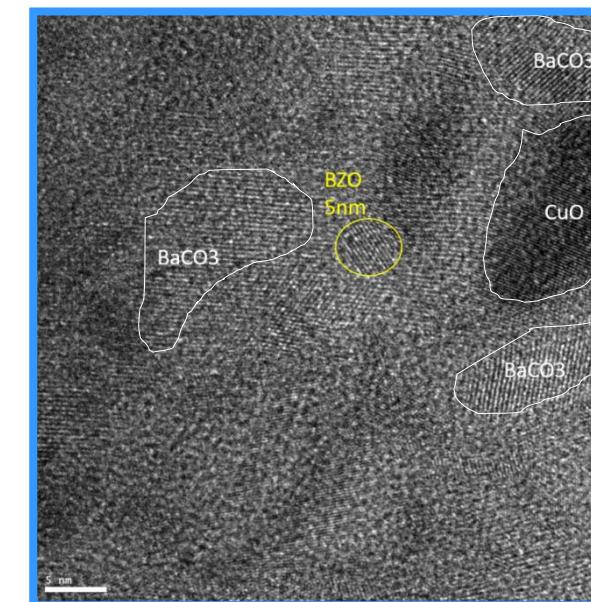
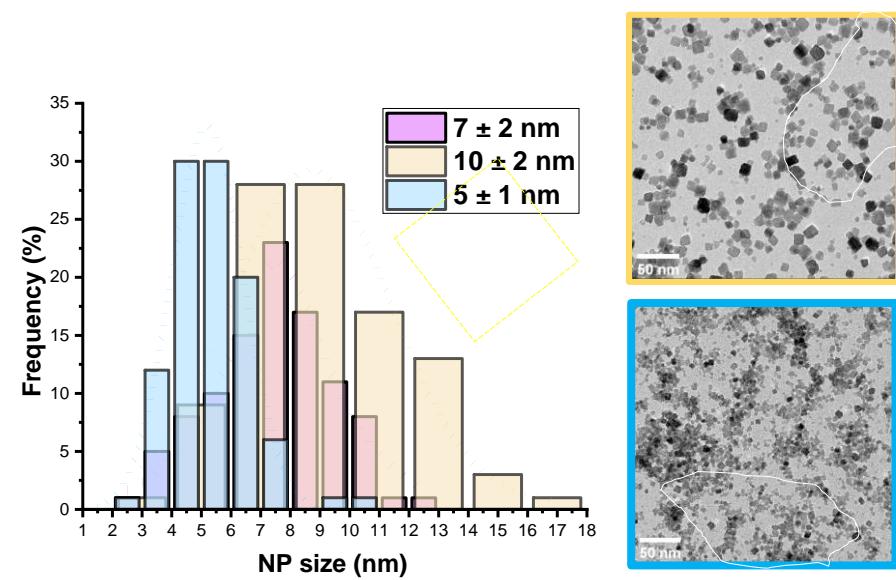
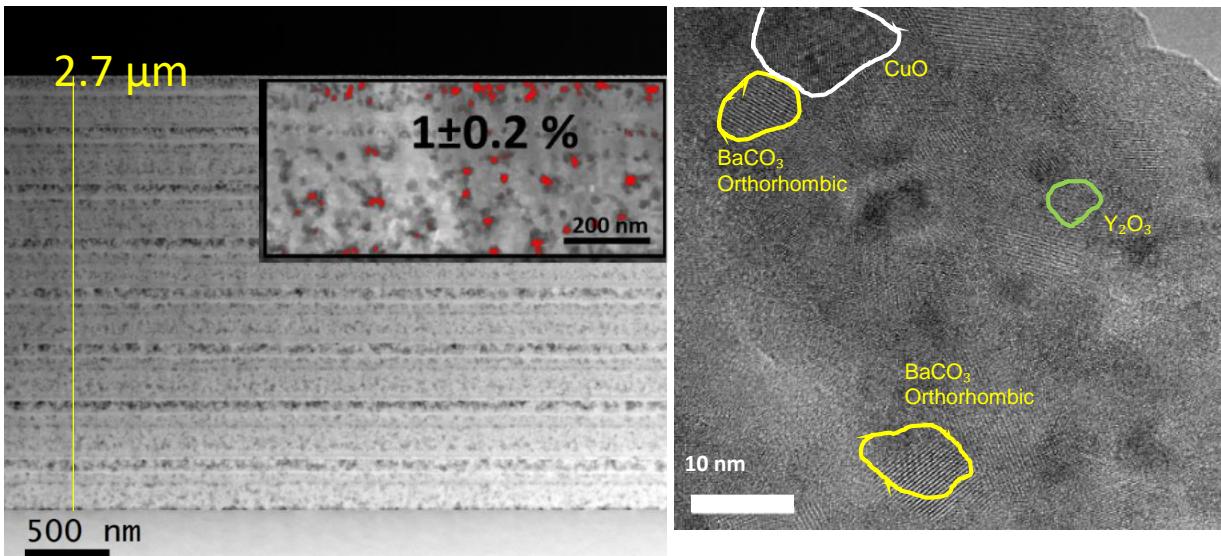
- Fast atomic diffusion
- Ultrafast growth rate, G , up to 2000 nm/s demonstrated
- Large area deposition
- Simple reactor
- High throughput
- Low cost/performance ratio

L. Soler et al., Nat Comm (2020)
S. Rasi, et al, Advance Science (2022)

CSD INKS AND PYROLYZED MULTIDEPOSITED FILMS



Patent EP22382741



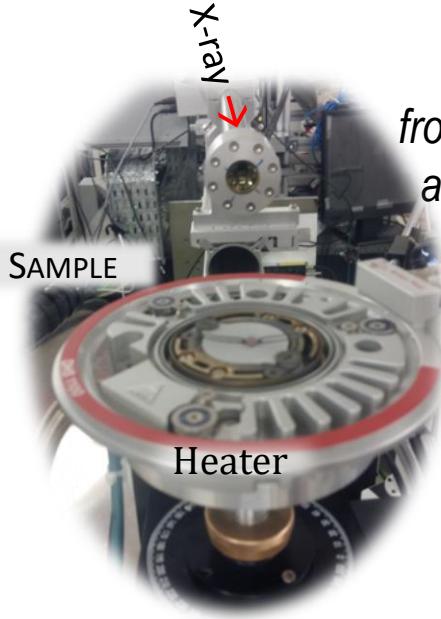
Multifunctional ink formulation

- Uniform pyrolyzed layers
- Low porosity
- Nanocrystalline and homogeneous
- Thickness beyond 3 μm tested
- BaCO_3 eliminated in TLAG

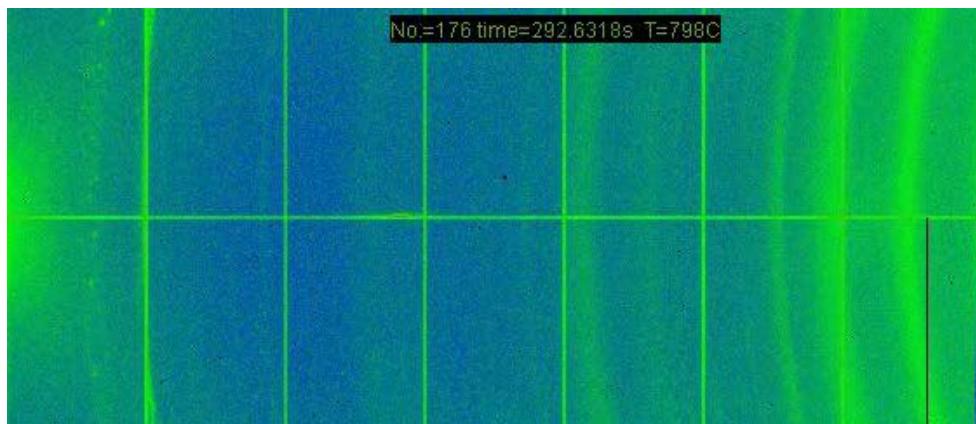
Multifunctional colloidal ink

- Hybrid Hydrolitic-Solvothermal Synthetic Process (H2S2)
- BaZrO_3 , BaHfO_3 Np
- Similar performance
- Crystalline BZO NPs retain their shape and small size in the pyrolysis

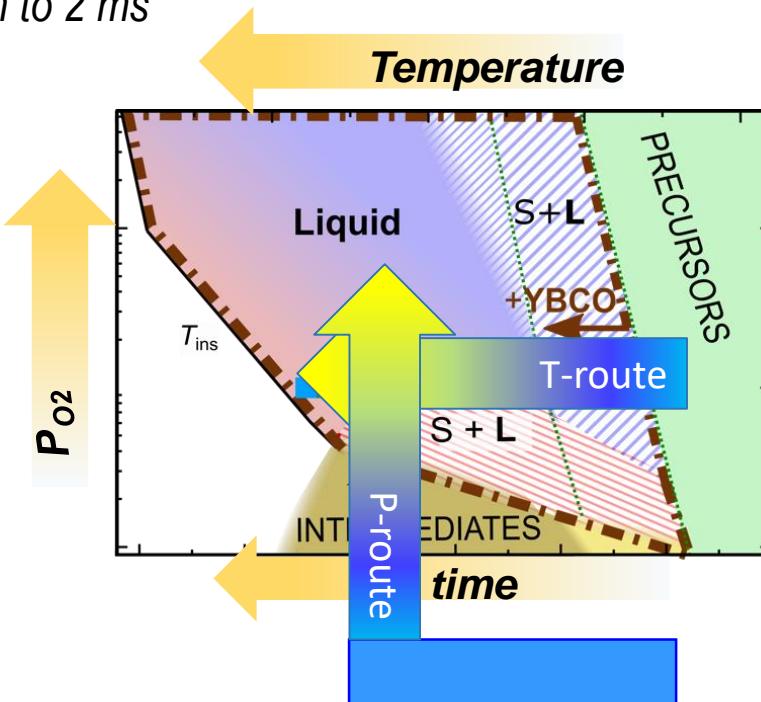
TLAG in-situ growth evaluation



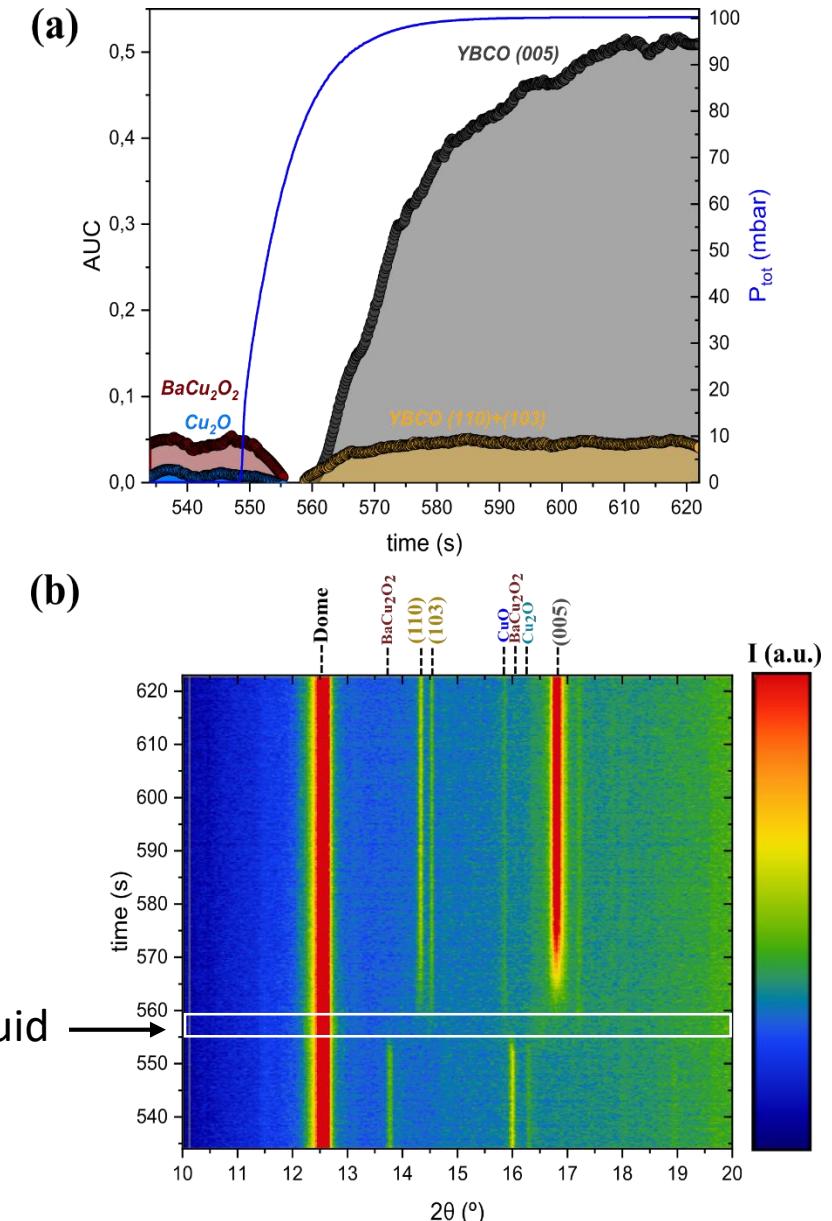
In-situ growth XRD
synchrotron experiments



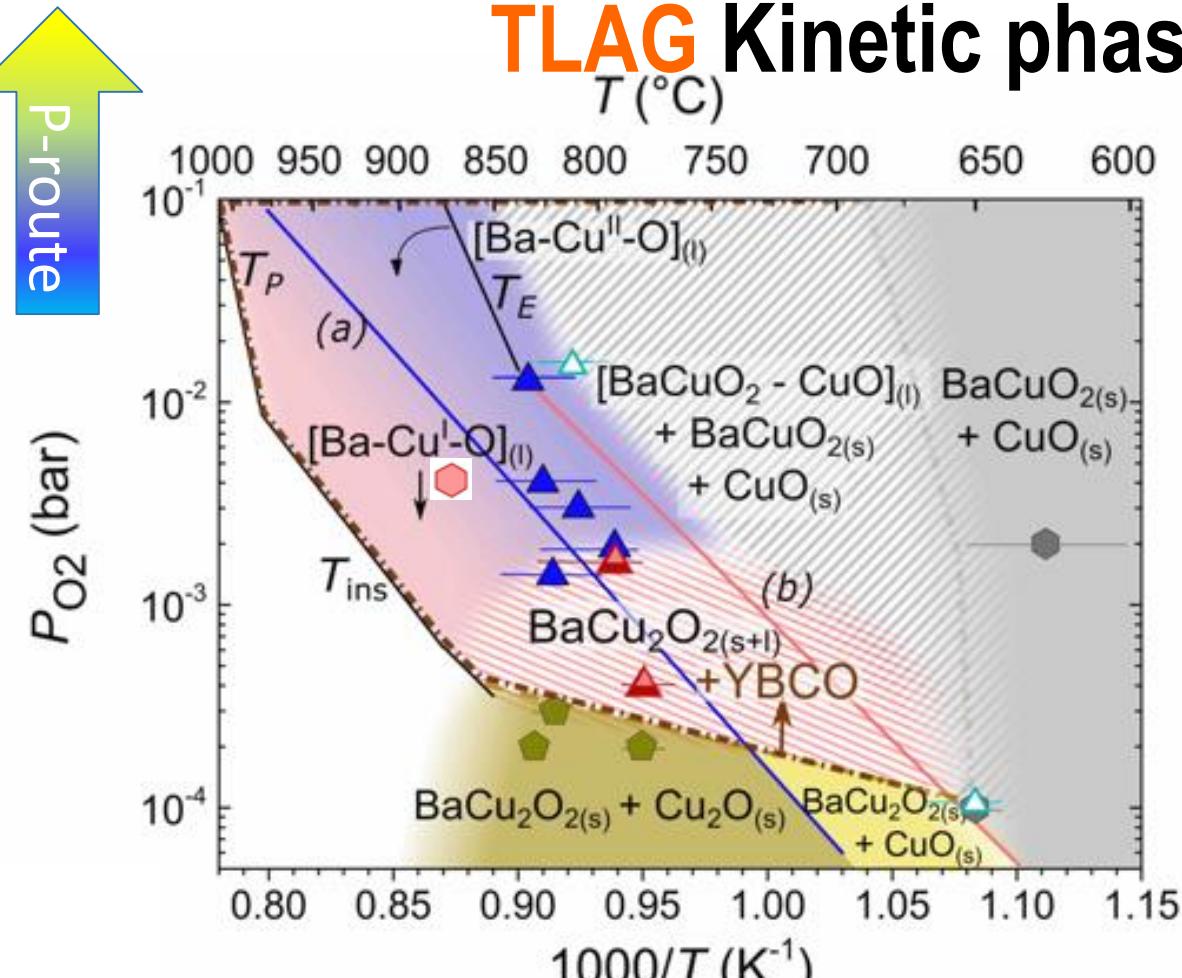
from 100 ms down to 2 ms
acquisition time



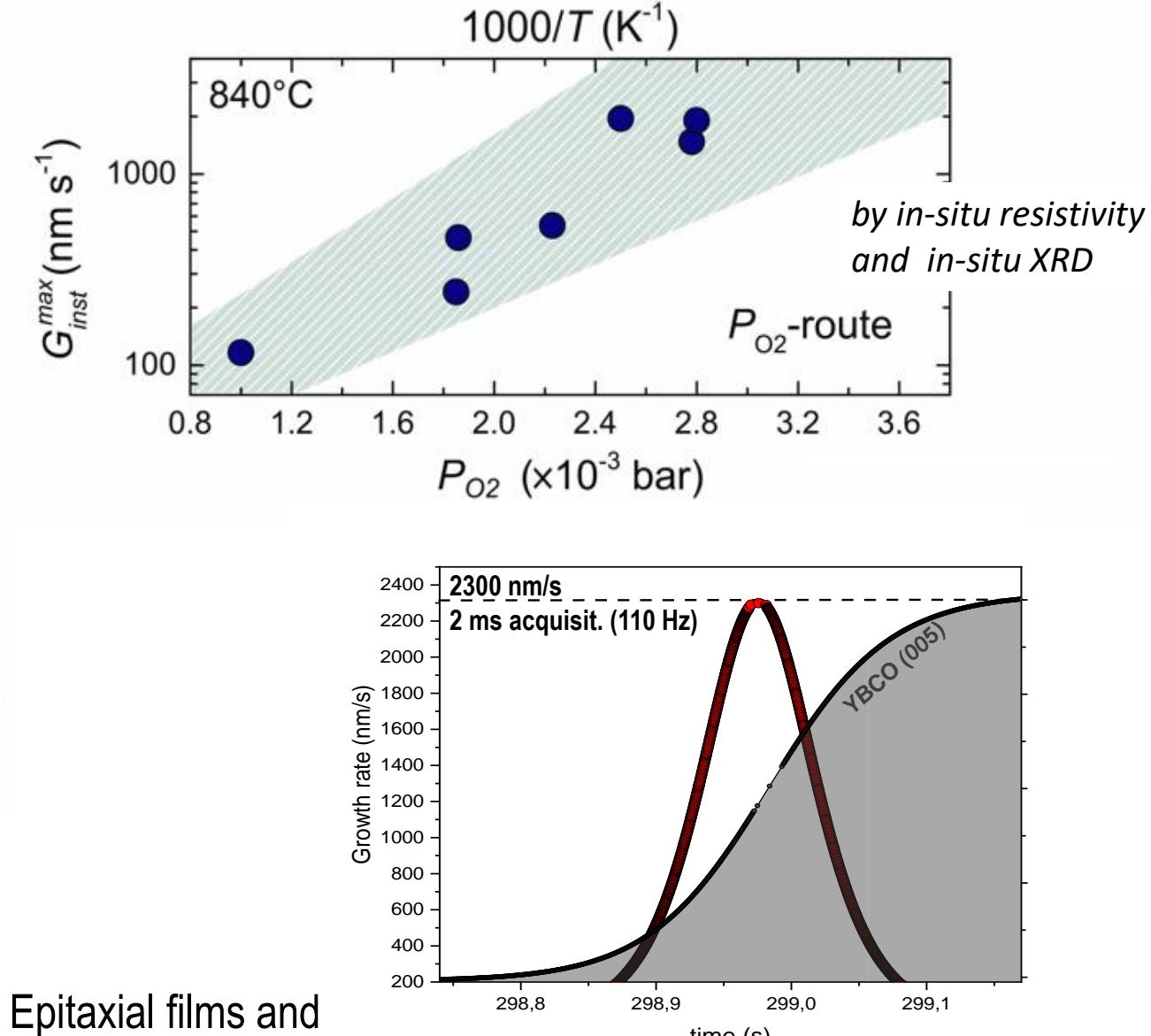
Transient liquid



TLAG Kinetic phase diagrams

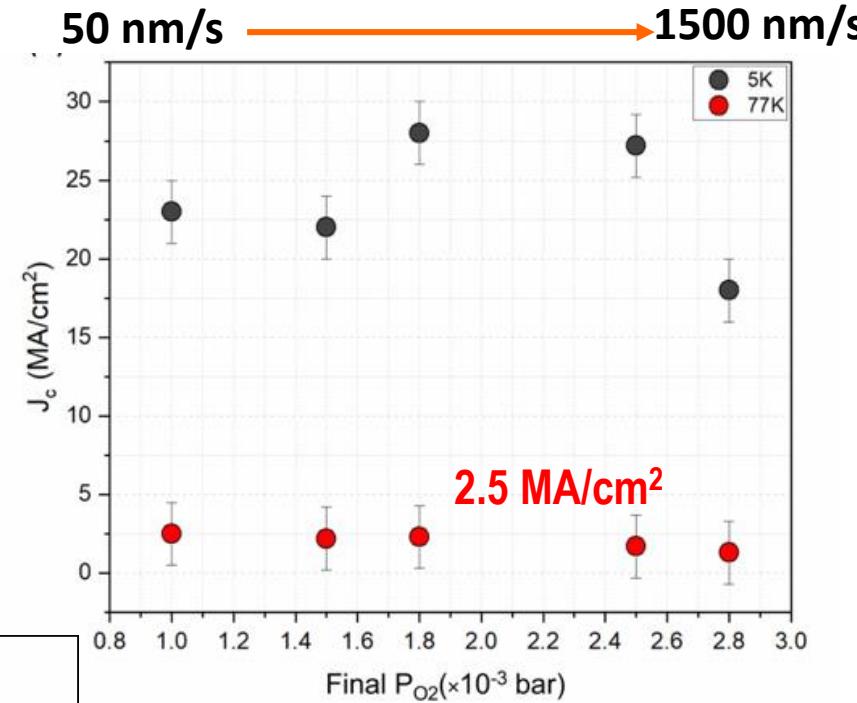
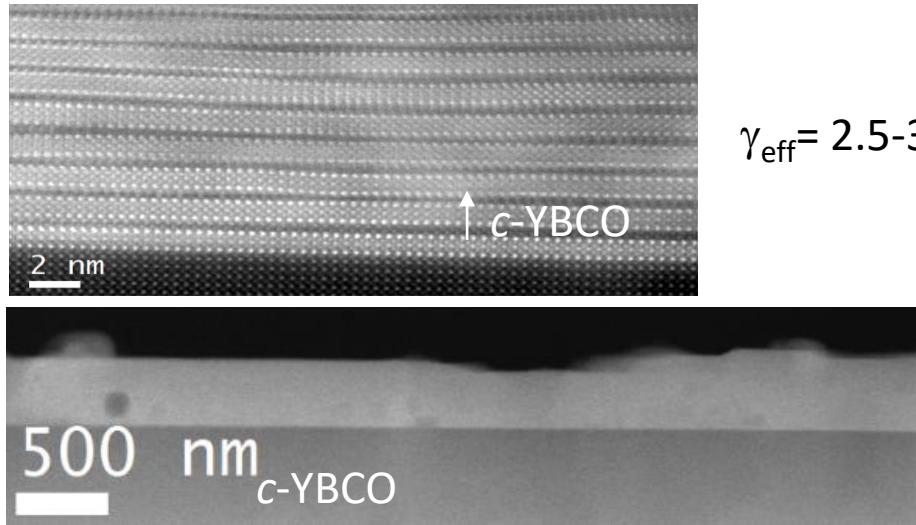
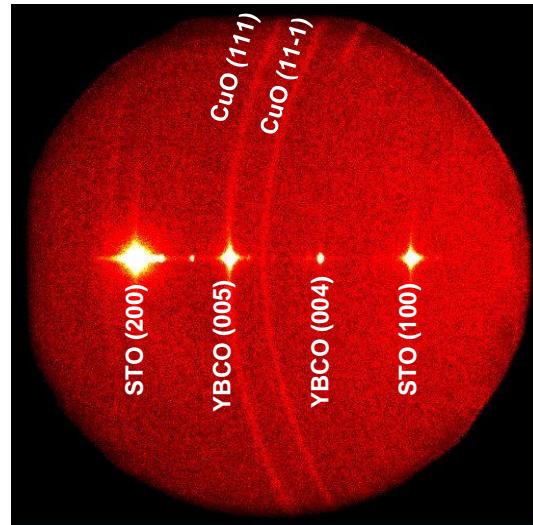


- ▲ $BaCuO_{2(s)} + YBCO + CuO_{(s)}$
- ▲ $YBCO + Cu_xO_{(s)}$
- ▲ $BaCu_2O_{2(s)} + YBCO + Cu_xO_{(s)}$
- ◆ YBCO
- T_E $BaCuO_{2(s)} + CuO_{(s)} \rightarrow [BaCuO_2 + CuO]_{(l)}$
- T_m $BaCu_2O_{2(s)} \rightarrow [BaCu_2O_2]_{(l)}$
- (a) $CuO_{(s)} \rightarrow Cu_2O_{(s)}$
- (b) $BaCuO_{2(s)} \rightarrow BaCu_2O_{2(s)}$

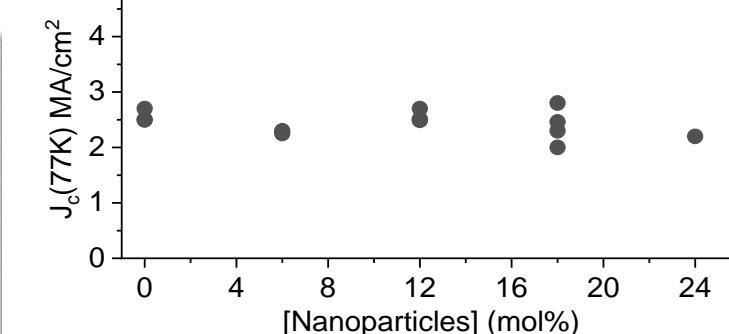
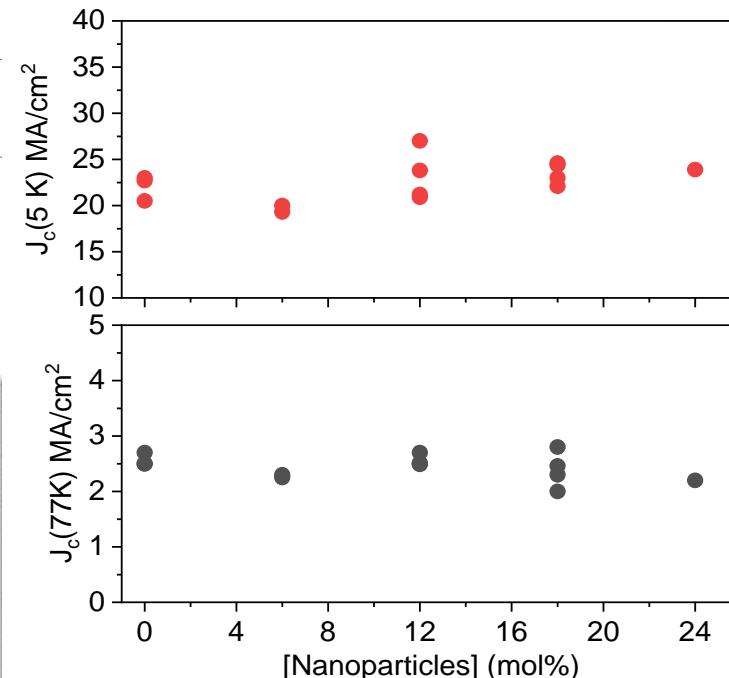
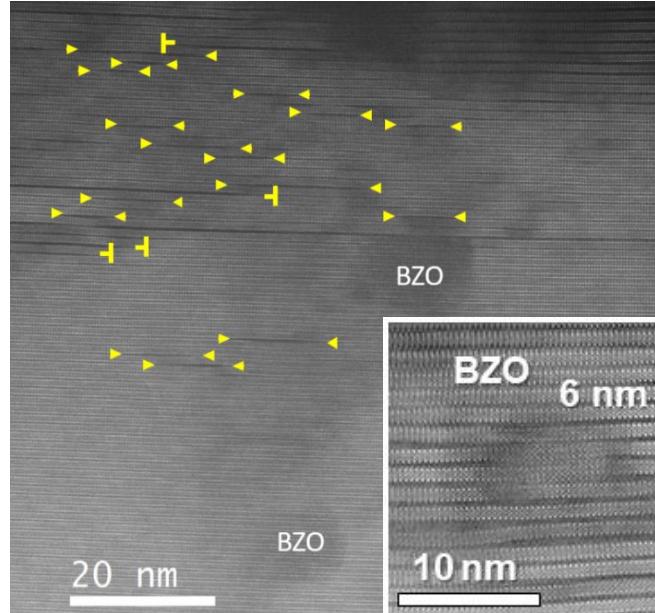
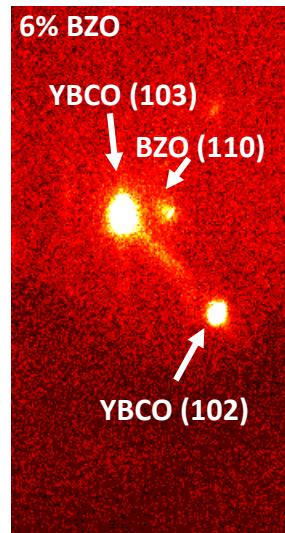


Epitaxial films and
nanocomposites at 2000 nm/s

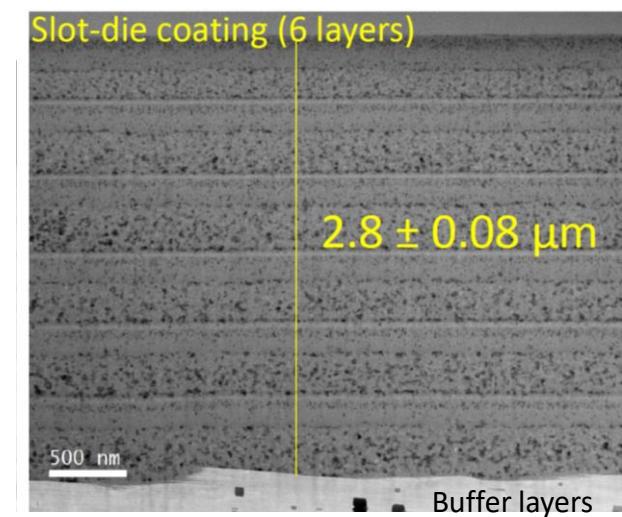
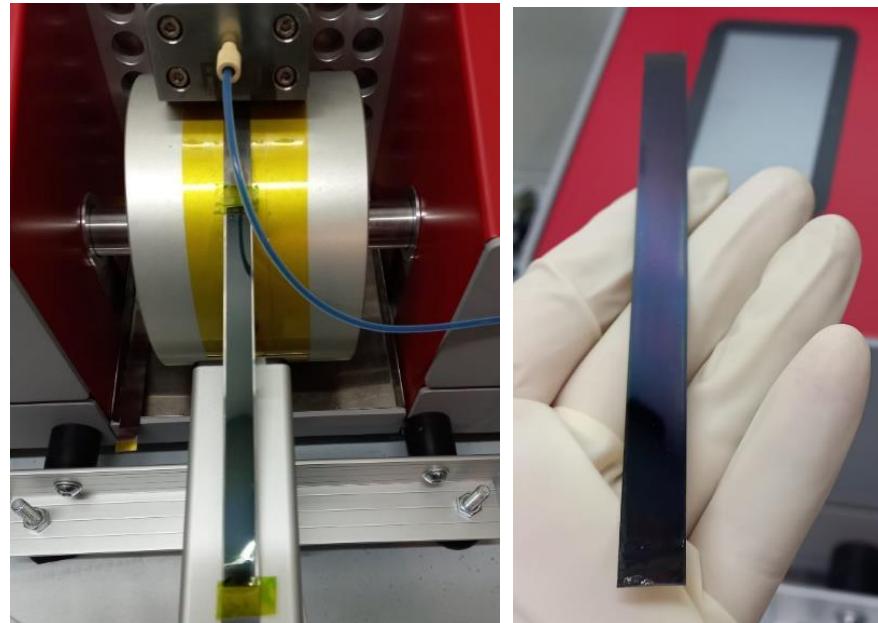
YBCO TLAG-CSD FILMS



Nanocomposites

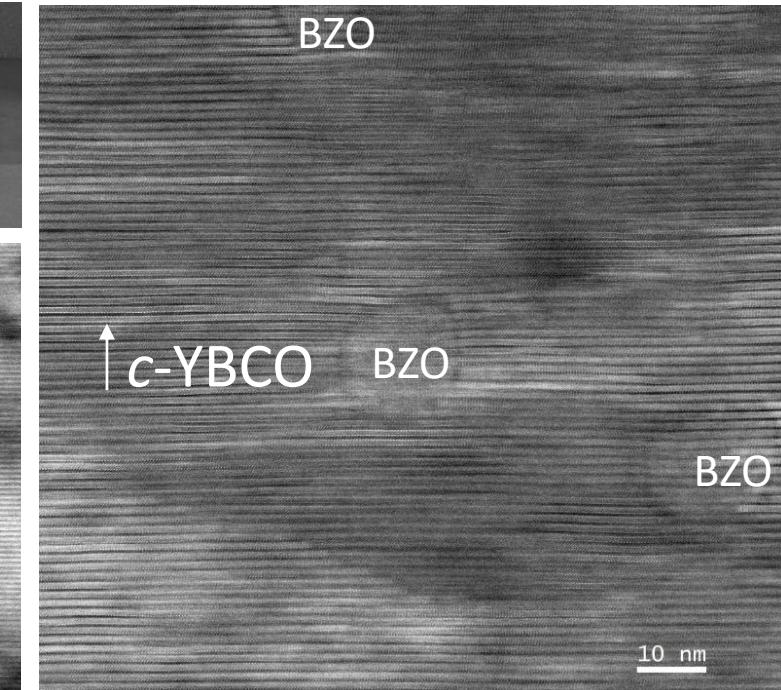
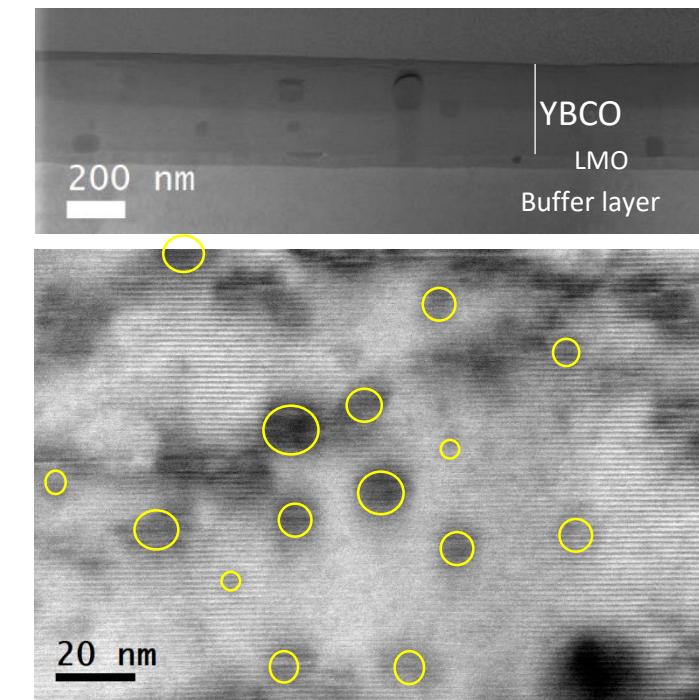


YBCO TLAG-CSD NANOCOMPOSITE FILMS



Extended to technical substrates
in collaboration with

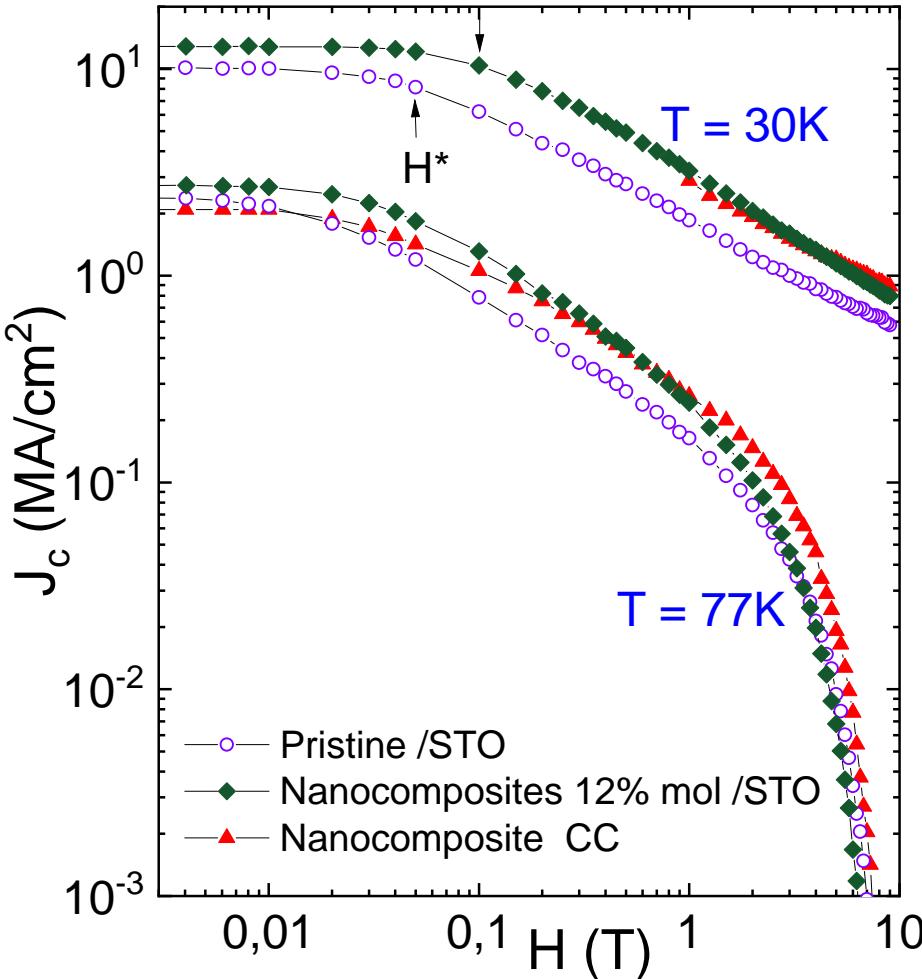
**SUMITOMO
ELECTRIC**



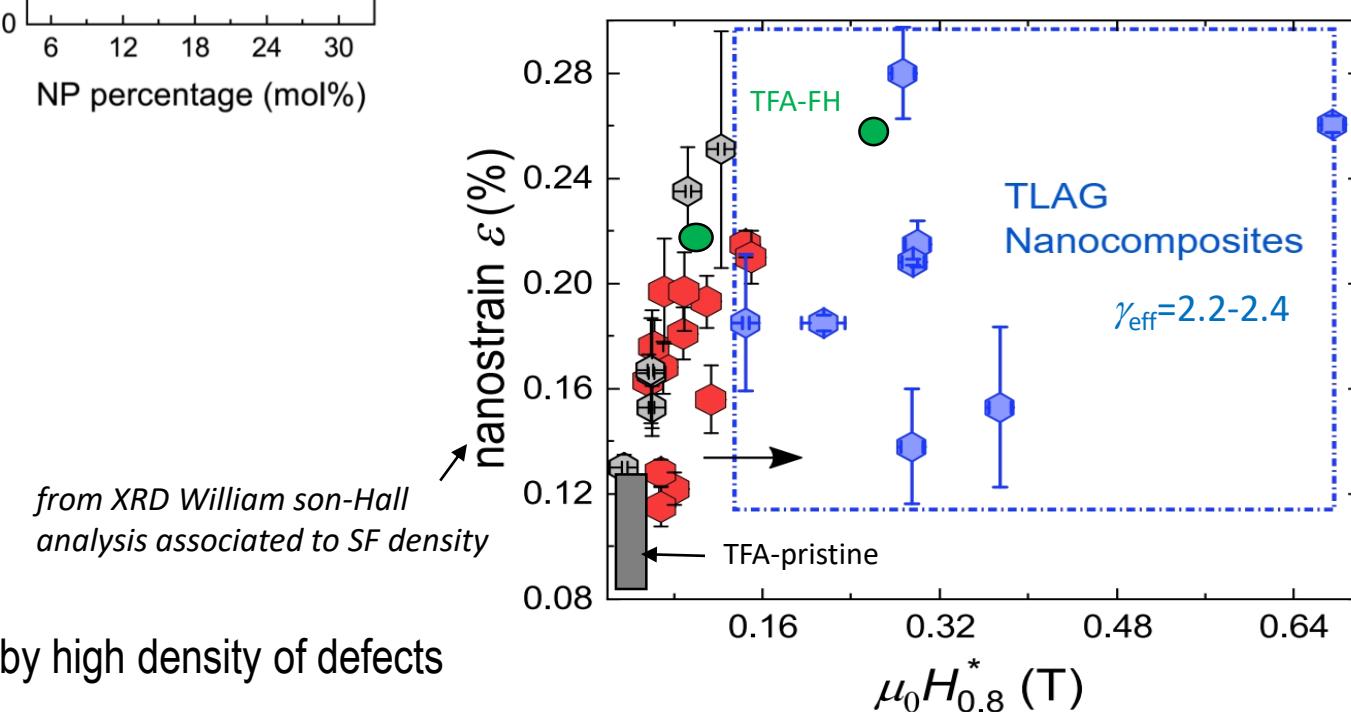
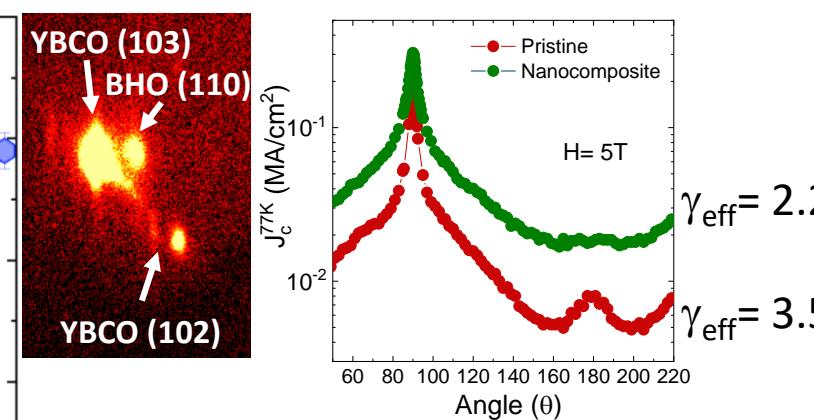
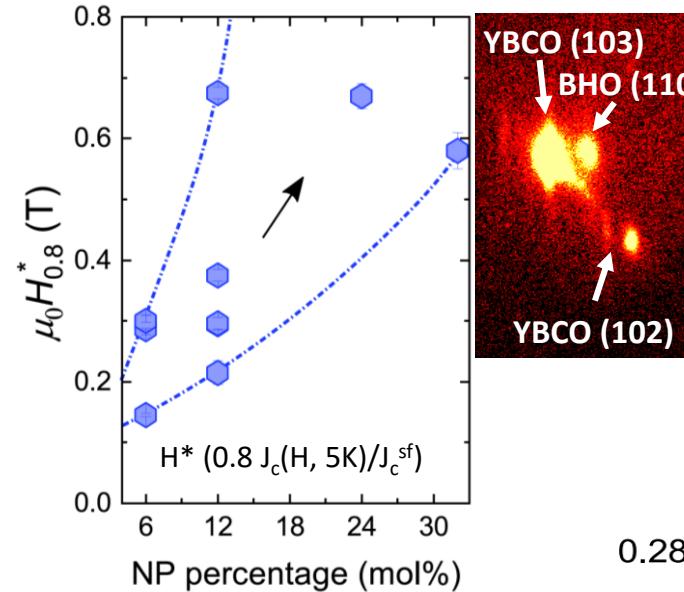
$$J_c(5\text{K}) = 24 \text{ MA/cm}^2 \quad J_c(77\text{K}) = 2 \text{ MA/cm}^2, I_{c, 750 \text{ nm}}(77\text{K}) = 130 \text{ A-w}$$

High density of defects is present as well as embeded nanoparticles

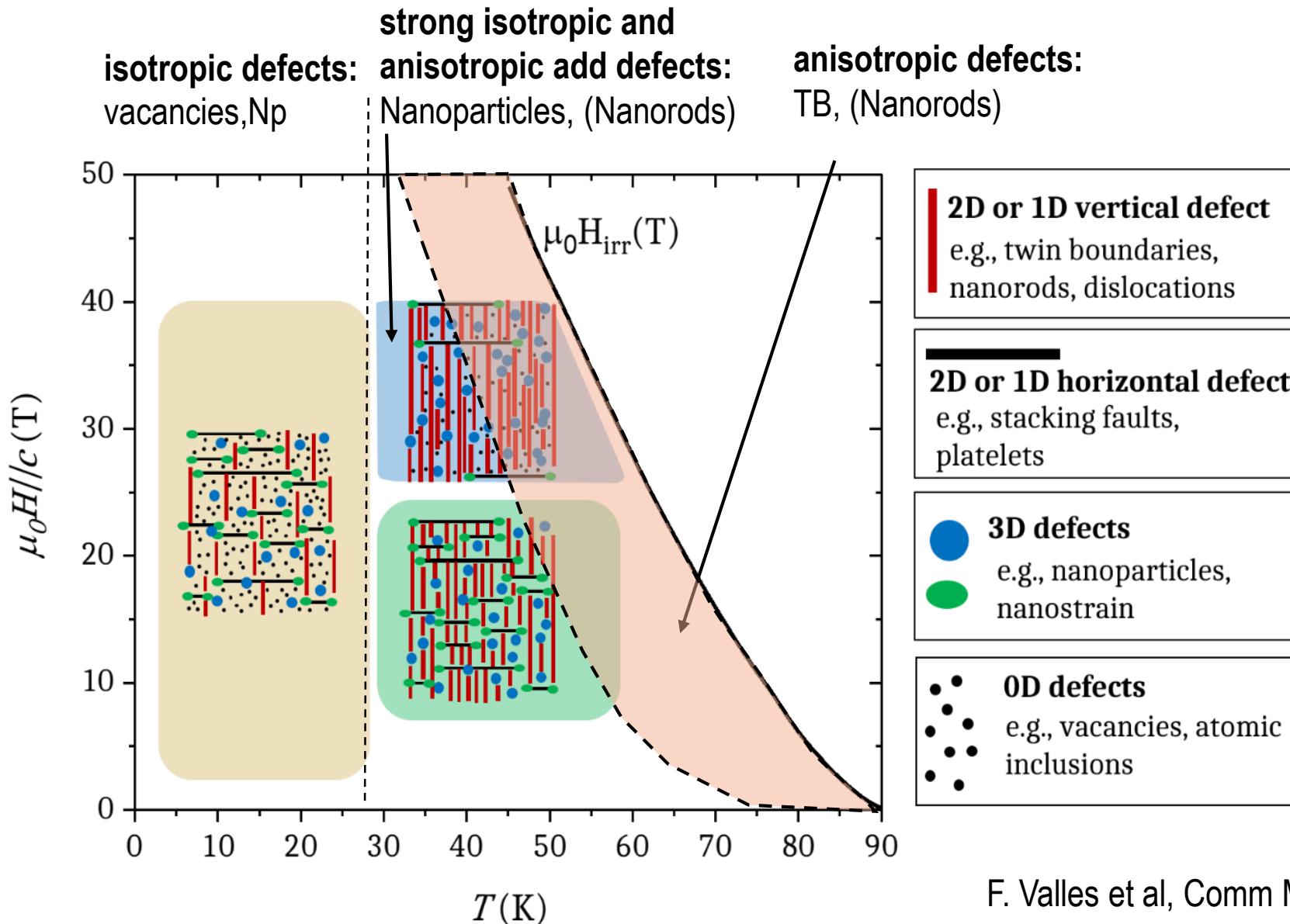
VORTEX PINNING IN TLAG-CSD NANOCOMPOSITE FILMS



TLAG films respond to vortex pinning determined by high density of defects (SF, point vacancies) and nanoparticles



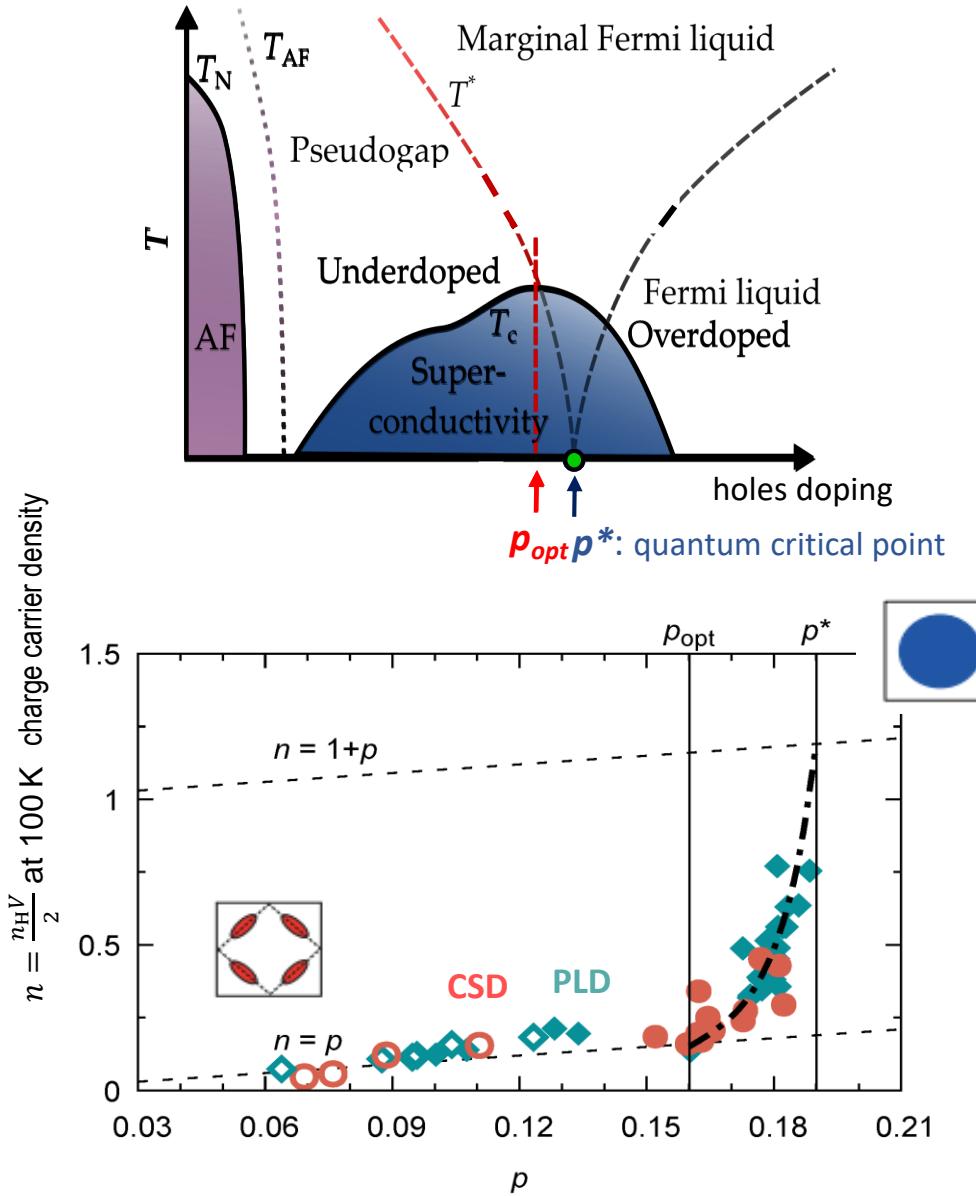
OPTIMIZING PINNING LANDSCAPES



NATIONAL HIGH MAGNETIC FIELD LABORATORY
D. Abaimov
J. Jaroszynski
D. Larbalestier

Different microstructure requirements for different regions

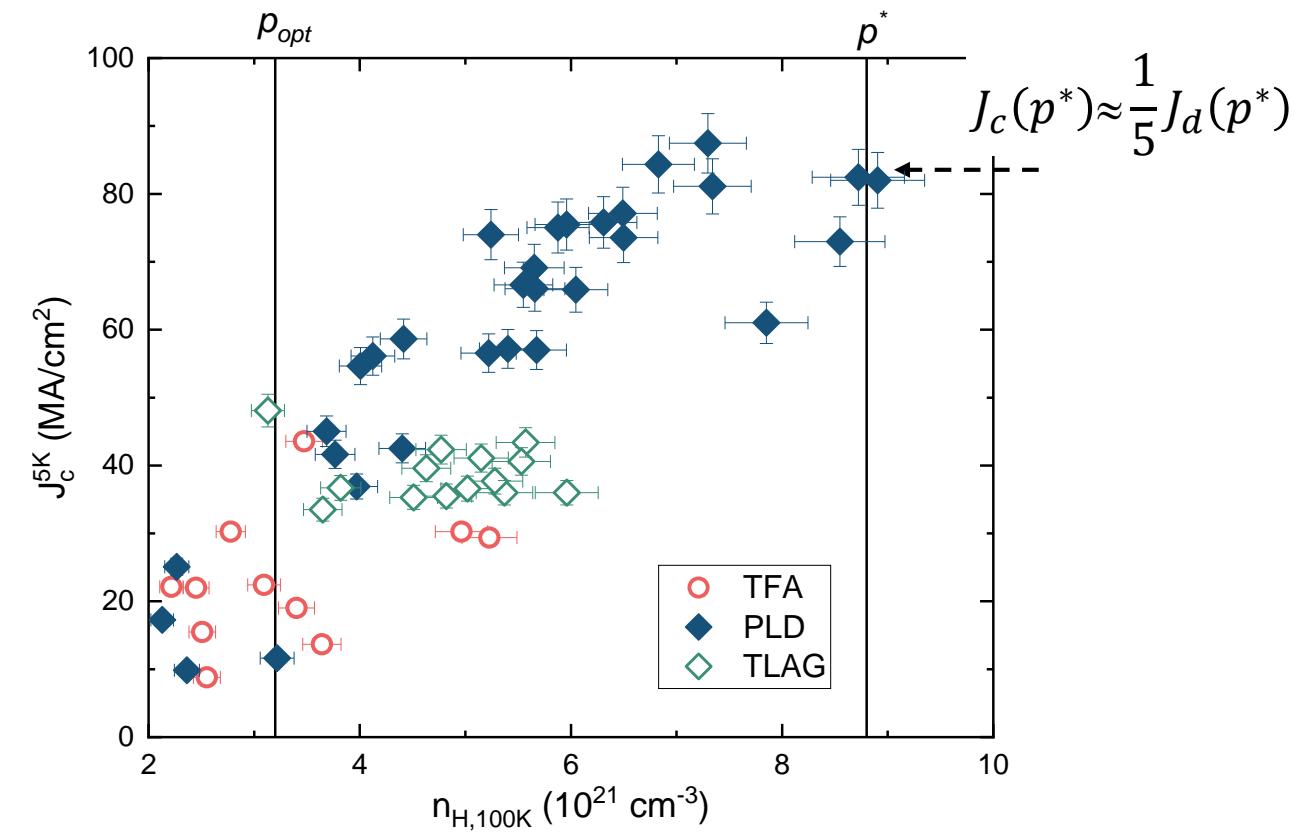
OVERDOPING: A ROBUST METHOD FOR PINNING



$$J_c^2 \propto n_H E_c(n_H)$$

A. Stangl et al, Sci. Rep. (2021)

Condensation energy and charge carrier density increases in the overdoped state



A. Stangl et al, Sci. Rep. (2021)

HIGH THROUGHPUT EXPERIMENTATION

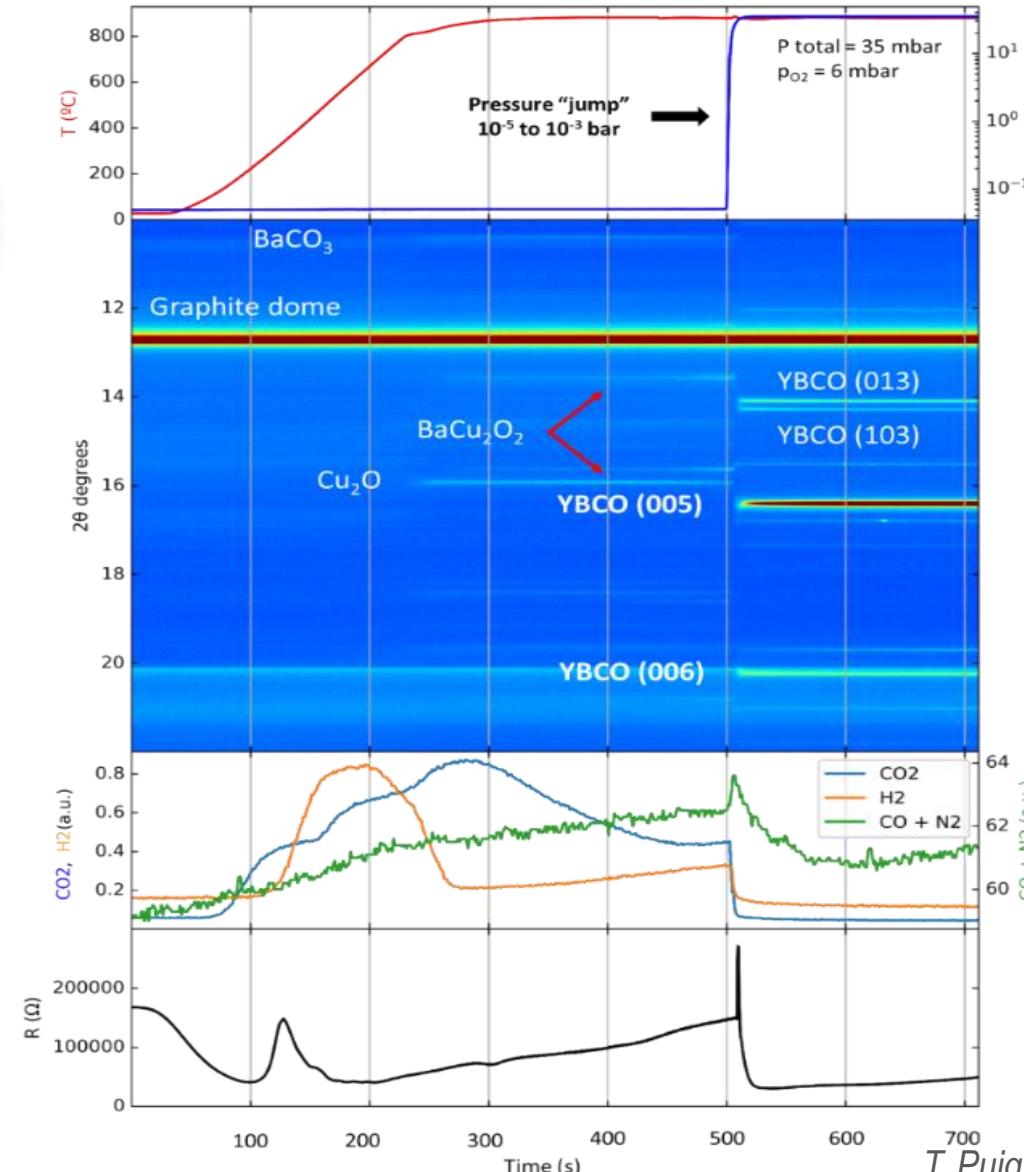
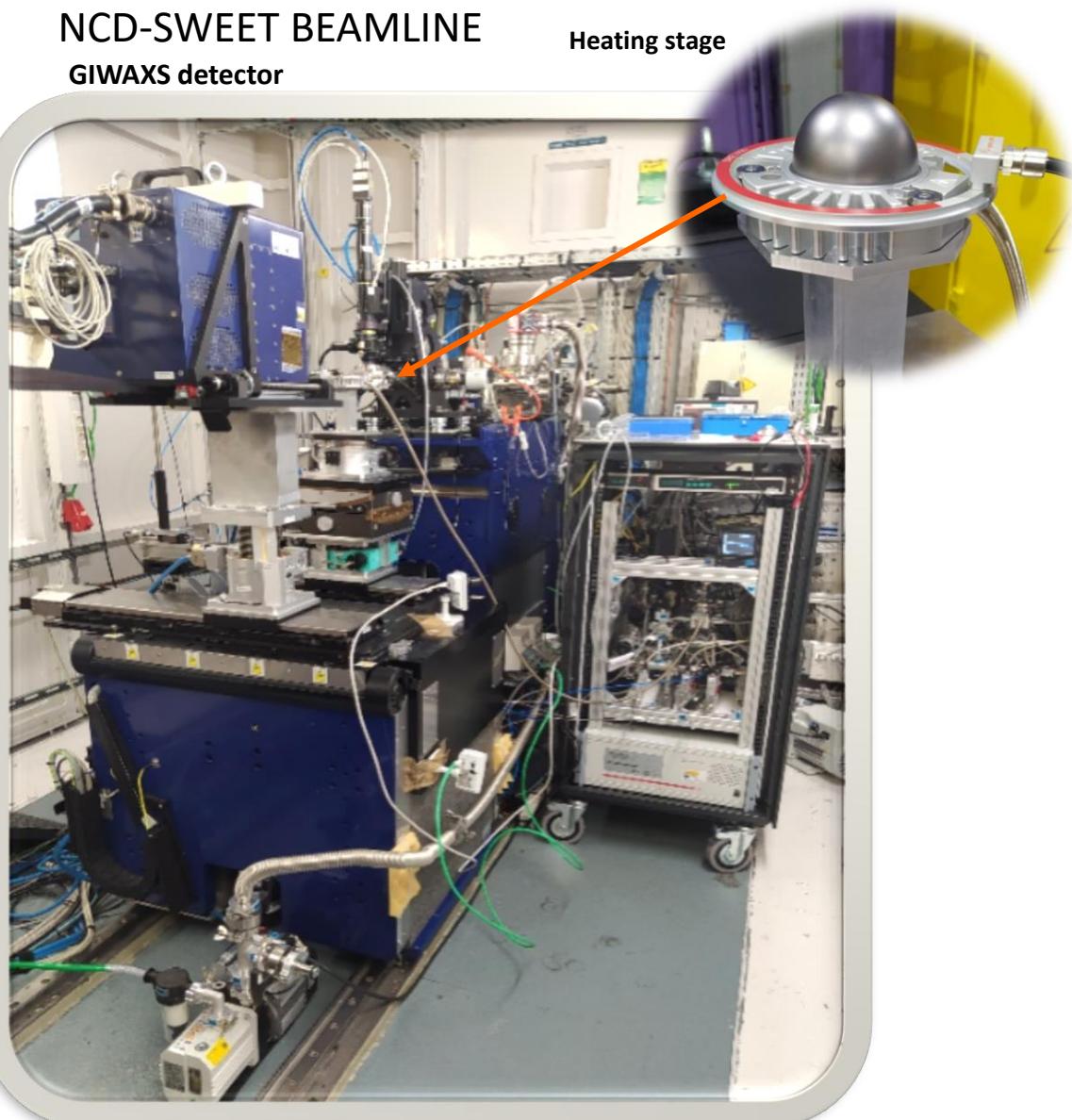


In-Situ ALBA Synchrotron installation

NCD-SWEET BEAMLINE

GIWAXS detector

Heating stage



Experiment conditions

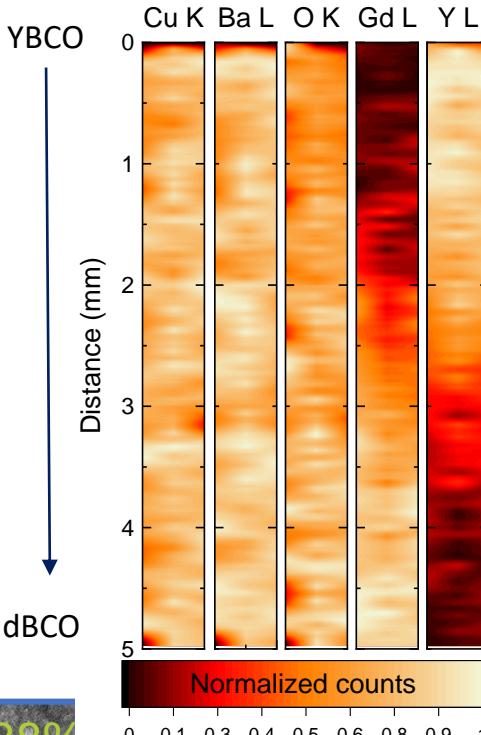
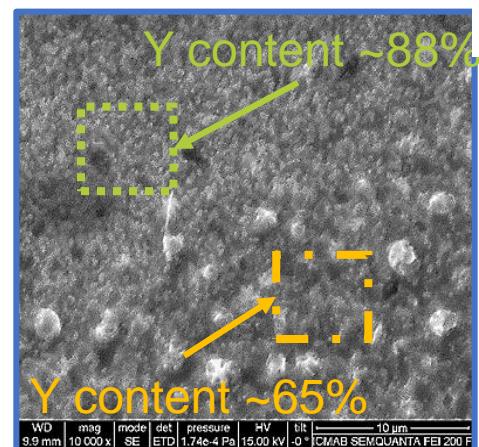
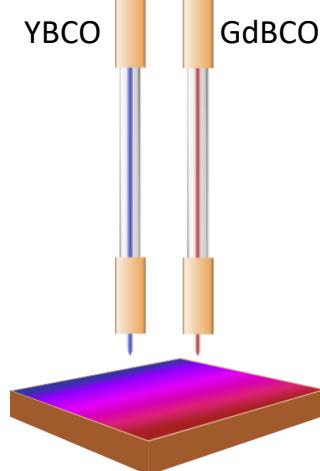
Synchrotron XRD

Mass spectroscopy

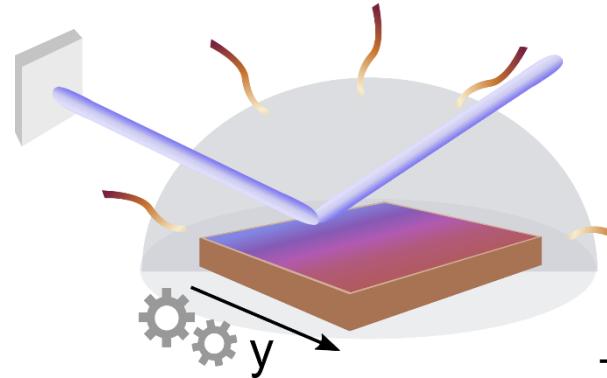
Resistivity

Fast optimization using Compositional Gradients

Combinatorial DoD Ink Jet Printing



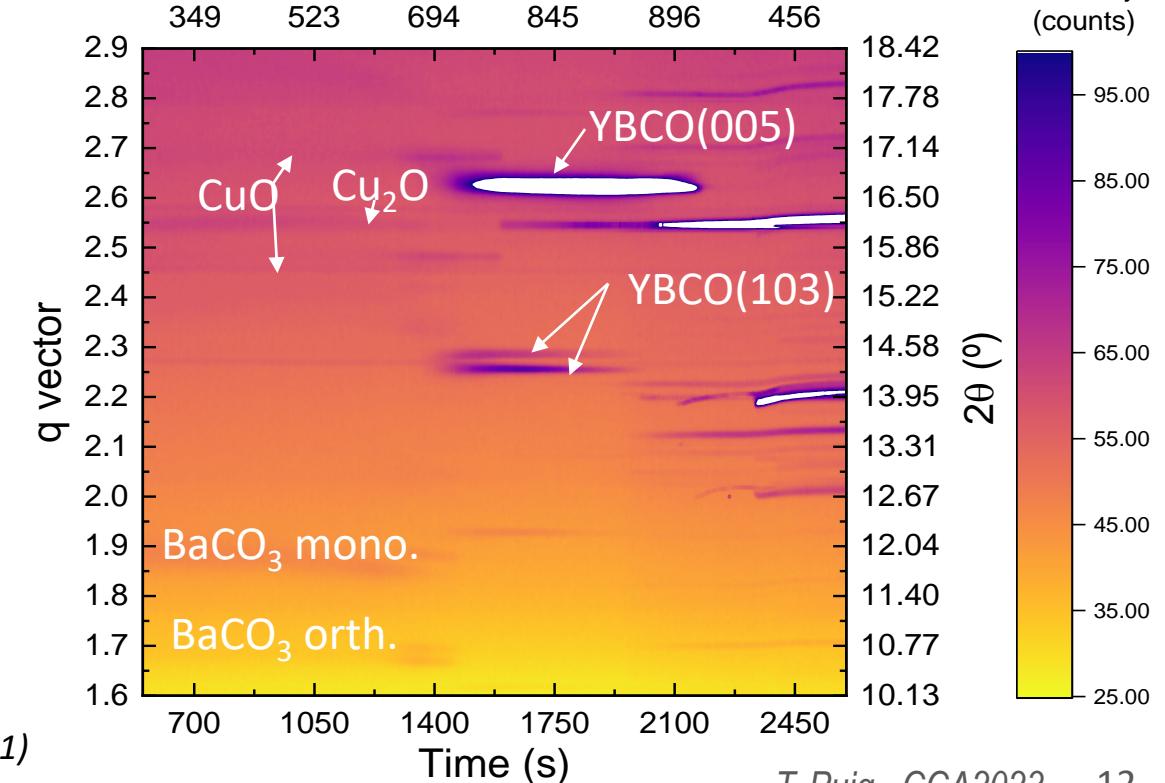
in-situ synchrotron XRD



Data is segmented by positions for analysis

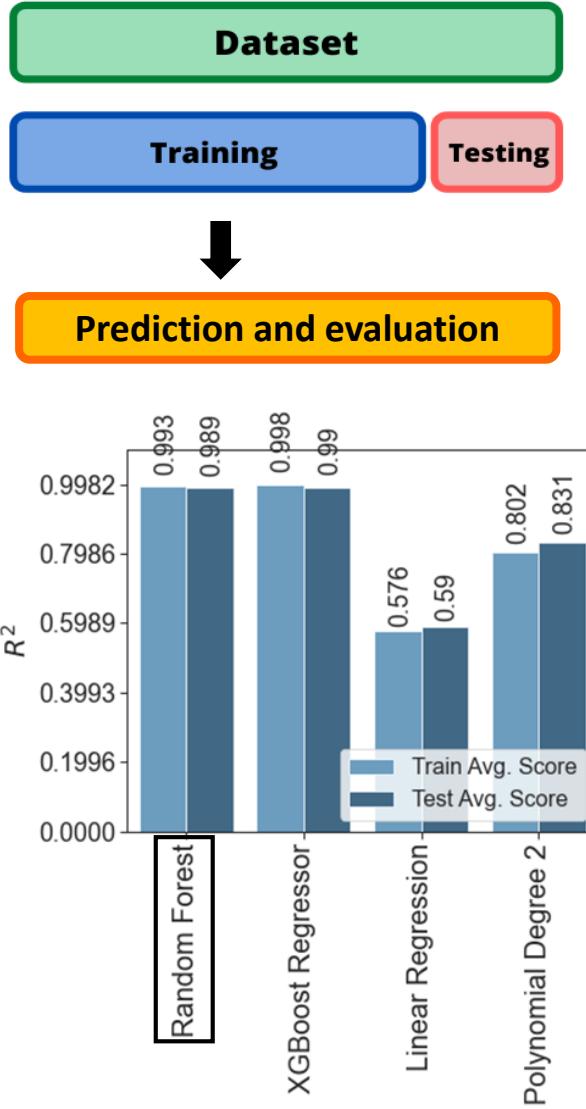
Case position 1

Temperature (°C)

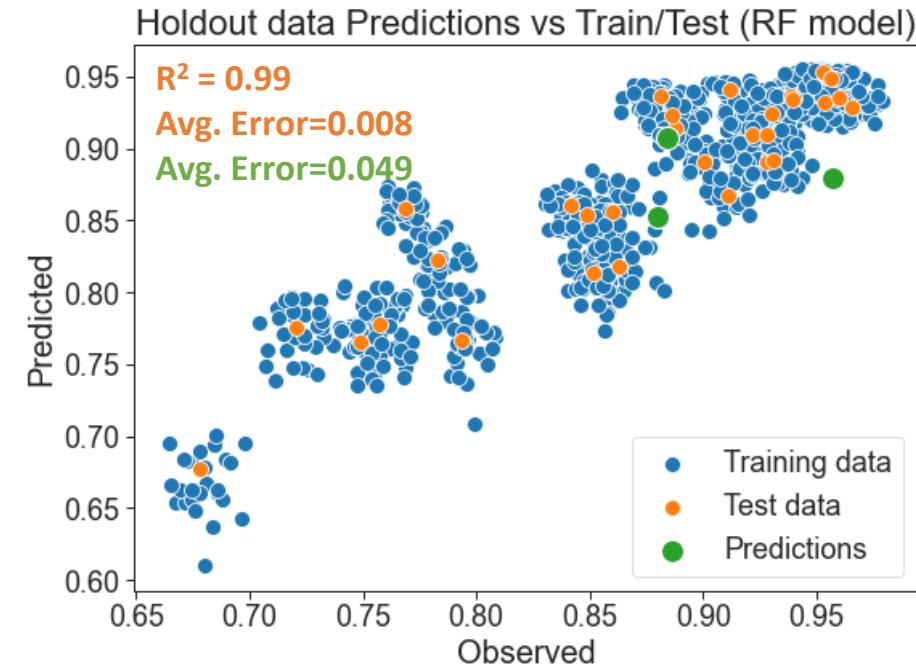
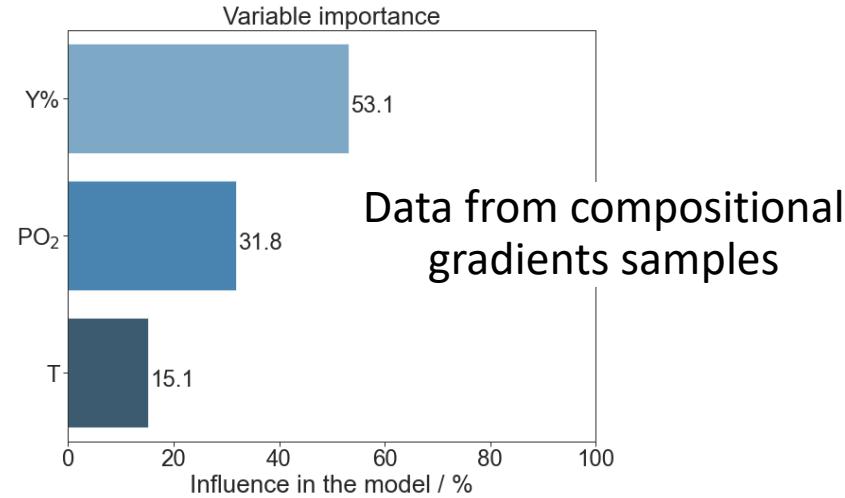




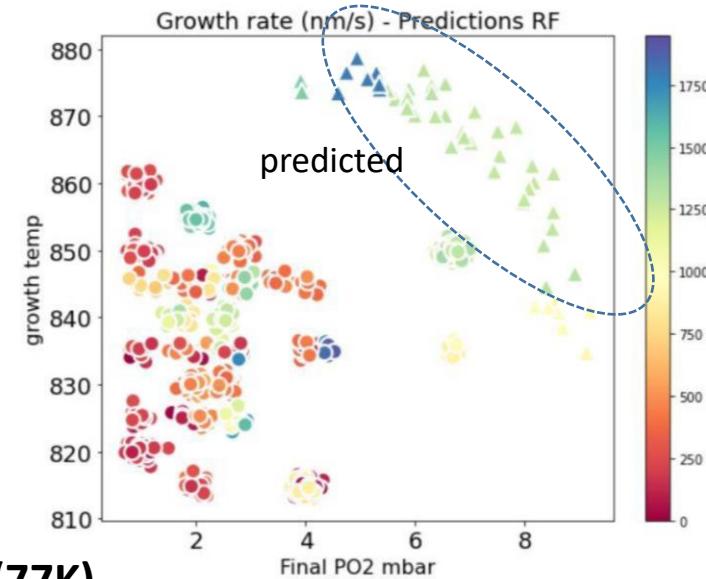
Machine Learning for fast guideness



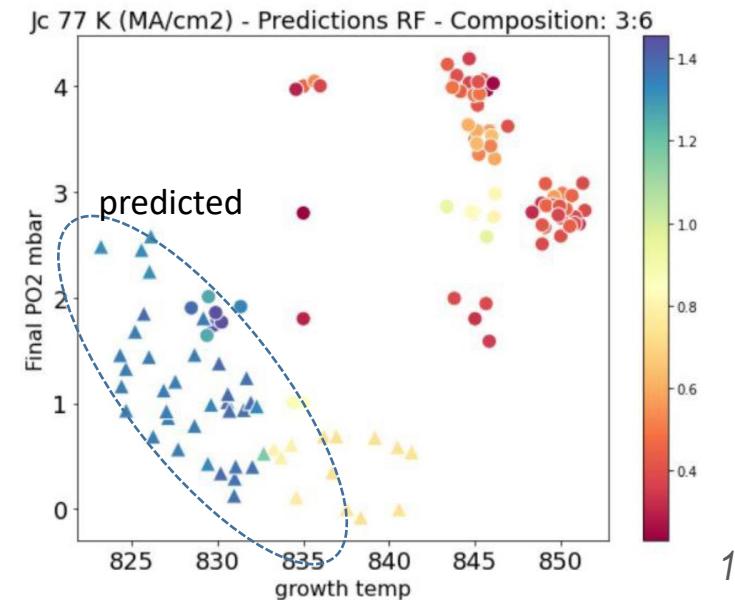
Optimizing c-axis growth by ML



Growth Rate



$J_c(77K)$



Conclusions

- TLAG is a non-equilibrium growth methodology with ultrafast growth rates achieving high performance Coated Conductors compatible with CSD
- In-situ synchrotron XRD experiments have been essential to understand the kinetic growth mechanisms and obtain epitaxial layers at ultrafast growth rates
- Pinning landscapes can be optimized at different regions depending on applications needs, overdoping being very appealing
- High Throughput Experimentation initiatives are foreseen to fasten optimization schemes
- Industrialization of TLAG should lead to a high throughput manufacturing process which uses simple and large area reactors for R2R CC production

Contributions from CC Materials Research

